

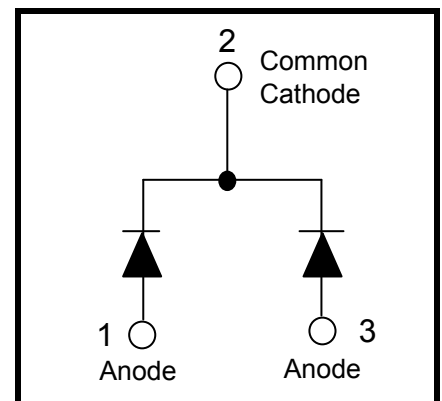
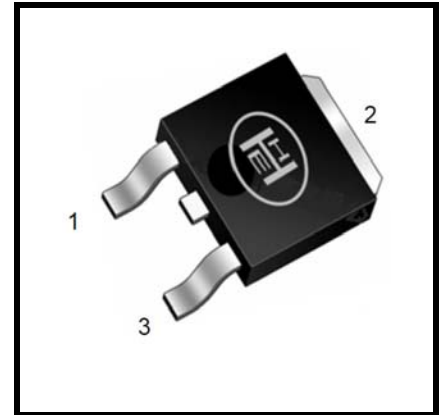
This series uses the Schottky Barrier principle with a platinum barrier metal.
These state of the art devices have the following features:

Features

- Schottky Barrier Diodes
- 20A Total (10A Per Diode Leg)
- Guard Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V 0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Shipped 50 units per plastic tube
- Pb Free Packages are Available*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.2 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and
- Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
 - 260°C Max. for 10 Seconds



■ MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	S20C60D	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Maximum Instantaneous Forward Voltage ($i_F=10\text{Amps}$, $T_C=25^\circ\text{C}$)	V_F	0.72	
Average Rectified Forward Current (Rated V_R) $T_C=133^\circ\text{C}$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20kHz) $T_C=133^\circ\text{C}$	I_{FRM}	20	
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I_{FSM}	200	
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0kHz)	I_{RRM}	5	
Operating Junction Temperature	T_J	-65~+175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/ μs

■ ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 125^\circ\text{C}$) (Rated DC Voltage, $T_C = 25^\circ\text{C}$)	i_R	6.0 0.05	mA
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■ THERMAL CHARACTERISTICS

Maximum Thermal Resistance Junction to Case Lead Temperature for Soldering Purposes: 1/8, from Case for 5 Seconds	$R_{\theta JA}$ $R_{\theta JC}$	60 2.0	$^\circ\text{C/W}$
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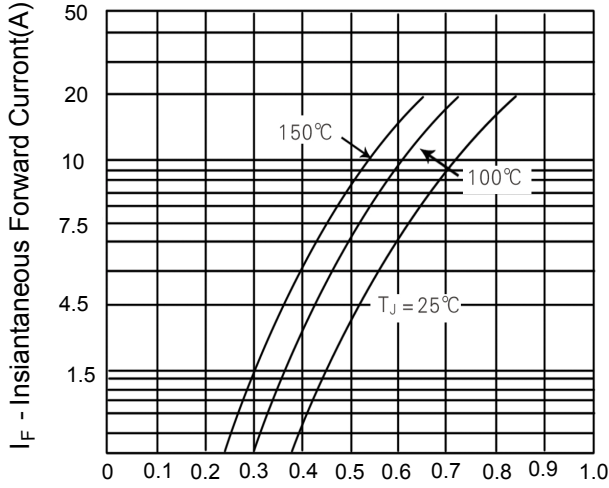


Figure 1. Typical Forward Voltage Per Diode

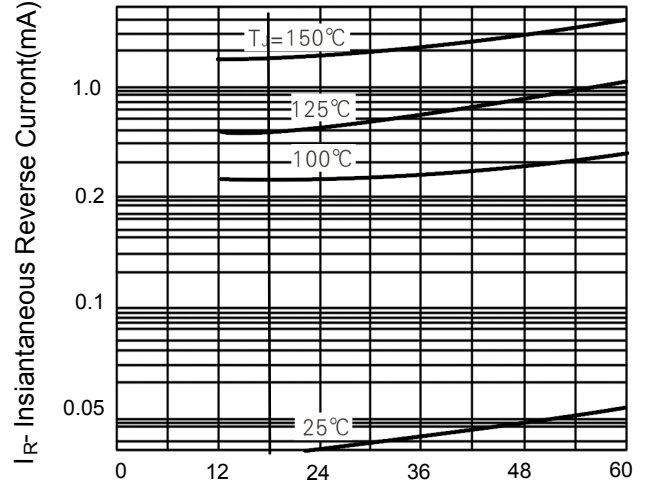


Figure 2. Typical Reverse Current Per Diode

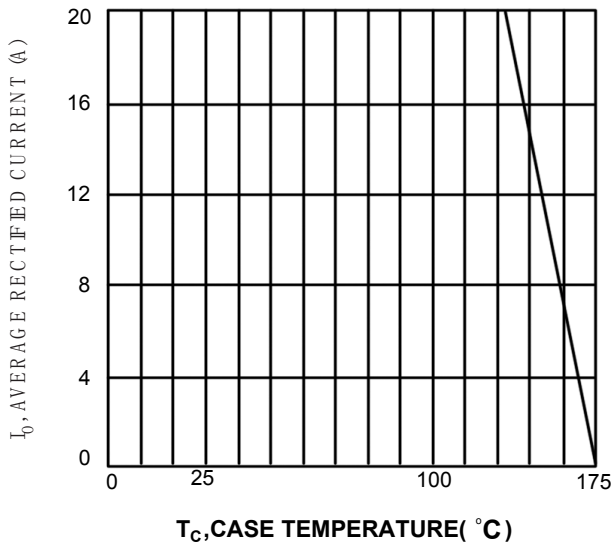


Fig.3 Forward Current Derating Curve

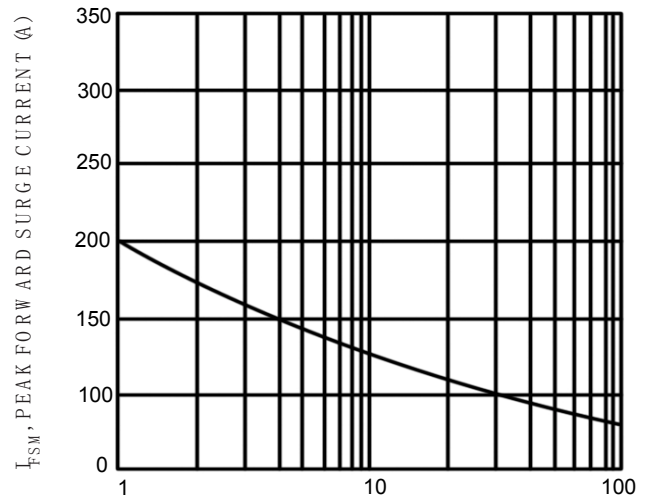
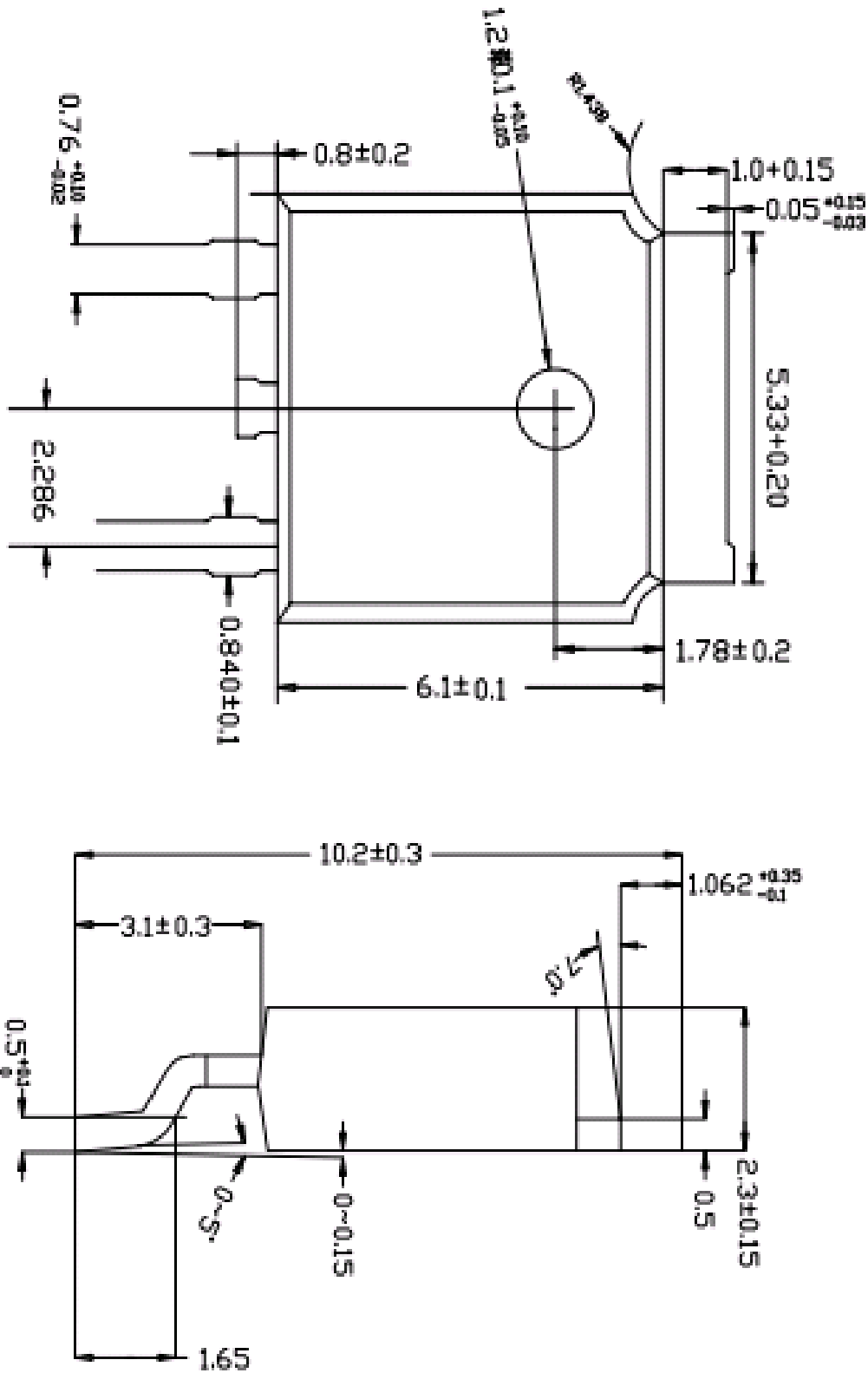


Fig.4 Max Non-Repetitive Surge Current

■ TO-252 (DPAK) Package Dimensions Dimensions in millimeters





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HAOHAI、HHE 图案、字母、均为我公司正式注册商标，仿冒、盗用均属侵权，违法必究！

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